Health Monitoring of digitally controlled flexible converters

Final Review 25/04/2024

0



ູ່ທີ່ໃຈໃ

Universidad Carlos III de Madrid



Universidad de Oviedo Universidá d'Uviéu University of Oviedo

Health Monitoring of digitally controlled flexible converters

Introduction



Universidad Carlos III de Madrid





Universidad de Oviedo Universidá d'Uviéu University of Oviedo

Introduction



- Each block is mission-dependent
- Long design times
- MEA is a centralized controller. Critical



• What if we could standardize and parallelize each main block (SAR, BCR, BDR)?

Supervisor

- Same hardware for each role (SAR, BCR, BDR)
- Control and protection local to each module
- Redundancy at module level
- Automatic power sharing
 - Failure recovery
 - Health monitoring to prevent failure
 - Power scale by introducing additional blocks

Universidad de Oviedo Universidá d'Uviéu

- No centralized controller
- Three branches to develop
 - Topology
 - Control Duriversidad Carlos III de Madrid
 - Health monitoring





Health Monitoring of digitally controlled flexible converters

Topology



Universidad Carlos III de Madrid



Universidad de Oviedo Universidá d'Uviéu University of Oviedo





- New architecture is proposed. Smaller units (modules) that can be combined to satisfy power needs
- 2. Each module can work as SAR, BDR and BCR
- 3. No hardware reconfiguration needed. Digitally controlled.
- 4. Redundancy at module level
- 5. No communication between modules
- 6. Additional supervisor module interfaces between power system and rest of spacecraft



- Topology selection based on a comparison of optimised converters (lowest losses for each point of operation).
 - Each module includes SAR, BCR, and BDR capabilities.
- Two-method analysis.
 - Qualitative analysis explores a wide range of converters

Supervisor

(Telemetry)

Quantitative analysis selects the best based on • a figure of merit





- Qualitative analysis
- Divided into: unidirectional, bidirectional and three-port topologies
- Evaluates adequacy of the topology (at module level) based on:
 - Number of semiconductor devices
 - Number of magnetic elements
 - Number of capacitors
 - Number of converters
 - Complexity of control
 - Bus limitations
 - Efficiency



| Topology | Converters total | Semiconductor devices | Inductors | Capacitors | Control | Bus lim. | Efficiency | |
|---|------------------|--------------------------|-----------|------------|----------------|----------|----------------|--|
| Buck or Boost | 3 | 12 | 3 | 6 | Simple | Y | Very High | |
| Weinberg | 3 | 21 | 6 | 6 | Simple | Y | High-Very High | |
| Non Inverting BuckBoost | 3 | 18 | 3 | 6 | Simple-Average | Ν | High | |
| Full Bridge | 3 | 24 | 6 | 9 | Simple | Ν | High | |
| Push Pull | 3 | 18 | 6 | 9 | Simple | N | High | |
| Bidirectional 2-level Switched-Capacitor | 2 | 16 | 2 | 8 | Complex | Y | High | |
| 4-switch BuckBoost | 2 | 12 | 2 | 4 | Average | Ν | High | |
| Bidirectional Buck/Boost | 2 | 8 | 2 | 4 | Average | Y | High | |
| DAB | 2 | 16 | 4 | 6 | Complex | Ν | High | |
| Bidirectional LLC | 2 | 24 | 10 | 8 | Complex | Ν | High | |
| ТАВ | 1 | 12 | 3 | 5 | Very Complex | Ν | High | |
| Interleaved Boosts with Full bridge (integrated) | 1 | 9 | 4 | 3 | Very Complex | Y | High | |
| Three-port asymmetrical Half Bridge | 1 | 8 | 2 | 4 | Very complex | Y | Medium-High | |



- Unidirectional:
- Offer no real advantage
- Bidirectional:
- More advantages at almost no cost
- Reduce number of modules in one
- Galvanic Isolation not a requirement. Increase in weight
- Three port bidirectional:
- Reduction of components
- Single control. More complex
- Modularity more cumbersome
- Final candidates: Bidirectional buck and 4-switch buck-boost



Quantitative analysis

- Used to obtain a final figure of merit to evaluate the best topology to choose.
- Converters optimized for lowest losses.
- Sweeping process.
- Optimised variables: fsw, current ripple.
- Topologies: Bidirectional buck and 4-switch buck-boost.
- Conditions:
 - Bus voltage: 28 V
 - Battery voltage 22 to 34 V
 - Solar array voltage: 30 to 60 V.
 - Power: 500 W.
 - Switching frequency: 30 to 200 kHz
 - Current ripple (relative): 0.05 to 0.45

Universidad de Oviedo Universidá d'Uviéu University of Oviedo

- Definition of input variables (voltage range, power, switching frequency, current ripple, etc)
 - 2. Minimum inductance value
 - 3. Switch selection
 - 4. Inductor design
 - 5. Rough estimation of efficiency for each fsw-ripple pair
 - 6. Accurate efficiency estimation
 - 7. Figure of merit efficiency/weight









- Single point failure free
- Local OCP, UVP, OVP protections.
 - Protection FETs included.
 - In failure module isolates from power system.
 - Rest of the modules compensate
- Each module is digitally controlled by FPGA.
- Interface to control:
 - Analog
 - Input/Output voltage and current
 - Inductor current
 - Digital:
 - On/Off
 - Transistor driving
 - Watchdog





- Watchdog prevents digital controller failure.
- If stuck permanently High or Low module isolates.





- Prototype built with COTS
 - Rad-hard equivalents available
 - Component availability
 - Switching elements: GaNSystems GS66516B



| Bus voltage | 100 V | | | |
|---------------------|---------|--|--|--|
| Battery voltage | 80 V | | | |
| Solar array voltage | 150 V | | | |
| Output capacitor | 35.2 μF | | | |
| Switching frequency | 180 kHz | | | |
| Inductance | 83 μΗ | | | |
| Current ripple | 2.5 A | | | |
| Output current | 5 A | | | |
| Bus power | 500 W | | | |





- Boost Mode
 - Vin=80 V
 - Vout=100 V

| | 50.0V/ | 2 20.07/ | 3 | .00A/ | 4 | 20.07/ | | 207.85 | 2.000%/ | ' Auto | t | 3 | 1.13A |
|------------|----------------------|-------------------|--------|-------|-------------------|--------|---|------------|---------|--------|---|---|-------|
| | Var | . (20 V/a | div) | | | | - | | | | | | |
| | <u>• BU</u> | 5(20 7) | , | | | | - | | | | | | |
| | V _{ВАТ} (2 | 0V/div) | | | | | - | | | | | | |
| | V _{DS HIGH} | . <u>(50 </u> γ/d | liv) | | | | - | → 2 | µs/div | | | | |
| | | | | | | | - | | | | | | |
| | | | + | | | | * | | | | | | |
| 1 ₽ | | | | | | ╞ | | | | | | | |
| 4⊉ | | | \sim | | 1 _L (1 | A/div | | \sim | | _/ | ~ | _ | |
| 7 | | \checkmark | | | | | | | | | | | |
| 3 ⊉ | | | | | | | - | | | | | | |

- Buck Mode
 - Vin=150 V
 - Vout=100 V









- Full power temperature response below 90°C.
- Full power efficiency:
 ~96%



Conclusions: Topology

Universidad de Oviedo Universidá d'Uviéu University of Oviedo University of Oviedo

- New power architecture is presented
 - Hardware developed to test it
- Allows parallelization and adequate power scaling
- Allows decentralized control
- M. Fernandez, M. Arias, P. F. Miaja, J. Oliver, J. A. Fernandez and P. Z. Vaquero, "Four-Switch Buck-Boost Based Module Block for Highly Modular Power Architecture," 2023 13th European Space Power Conference (ESPC), Elche, Spain, 2023, pp. 1-6, doi: 10.1109/ESPC59009.2023.10412700.



Health Monitoring of digitally controlled flexible converters

Control



Universidad Carlos III de Madrid



Universidad de Oviedo Universidá d'Uviéu University of Oviedo

Control. Outline



• Control principle: droop control, DBS



• Control architecture and implementation



• Results



Control. Decentralized control in multiple converter architecture



- Typical example in microgrids: droop control
- Droop resistance made by control
- It allows multiple converters connected to the same bus sharing load without any communication among them
- Limitations:
 - Every module provides current to the load according the control law: no power limitation per module
 - All modules regulate cooperatively the bus: no regulation of other quantities are allowed (input side of the module: battery, MPPT,...)



Equivalent circuit for module *n*



Universidad de Oviedo

DC BUS

Universidá d'Uviéu

University of Ovied

 $R_{dr,1}$

 $V_{ref,1}$

Universidad

Load

 P_2

 P_3

Carlos III de Madrid

Control. Operation modes of the modular system

- Depending on the bus voltage, the modules have different operating modes:
 - Bus mode \rightarrow voltage sources + Rdroop (source or load)
 - Device mode \rightarrow regulates voltage or current at its no-bus side • (device side)
- At least one module in bus mode to regulate bus voltage



Control. DC bus signalling

- Every module has a slightly different bus reference voltage
- Only one module regulates the bus
 SAR modules priority vs. Battery modules to the load deliver power to the load Bus
- SAR modules have the higher reference voltages
- When a module has a bus reference voltage lower than the actual bus voltage, it delivers the minimum output current: OA for SAR, OA or negative current for BCR
- When a given module reaches its maximum output current, it enters device mode

DC-Bus Signaling: A Distributed Control Strategy for a Hybrid Renewable Nanogrid

John Schönberger, Student Member, IEEE, Richard Duke, Member, IEEE, and Simon D. Round, Senior Member, IEEE



Universidad de Oviedo

Universidá d'Uviéu

University of Ovied

Universidad

Carlos III de Madrid

Control. Example of DC bus signalling





- provides the load power \rightarrow bus mode
- Module 1 reached its maximum power \rightarrow device mode
- Module 2 regulates the bus and provides the required extra power → bus mode
- Modules 1 and 2 reached their maximum power \rightarrow device mode
- Module 3 regulates the bus and provides the required extra power
 → bus mode

Control. Architecture overview









Control. Output current calculation





The output voltage is calculated from the sampled inductor current ADC with standard SPI







First order approximation to calculate the voltage reference from the calculated output current







Anti wind-up implementation (limits 0 and I_{max})



 The BCR charging reference current is provided by the supervisor using an additional block







Control. Seamless PWM, buck and boost

Universidad de Oviedo Universidá d'Uviéu University of Oviedo Universidad Carlos III de Madrid

34



Control. Seamless PWM, transition





Transition between buck and boost:







- Design debugging using co-simulation
 PSIM-Modelsim
- All control blocks implemented in VHDL
- Synthesis code included in simulation
- ADC model included in VHDL blocks

282


• Cosimulation has been essential to debug the control implementation



37

Control. Experimental set-up for single module





- A simplified power stage has been used:
 - Because of shortage of original GaN modules, • replacement for other equivalent
 - No auxiliary circuitry and protections •





IL3 Vbus Ibus Vin3



- V-I curve as expected
 - Droop control and DC bus signalling implemented
 - Admisible temperatura rise



Control. Single module: different input voltages





Different input voltage Medium bus current

Modulator demonstration







Control. Single module: input voltage sweep

Universidad de Oviedo Universidá d'Uviéu University of Oviedo Universidad Carlos III de Madrid



Ibus=2A

Bus voltage is properly regulated under input voltage slow variation

Control. Single module: load current steps







2

0.2

0.22

0.24

0.26

0.28

0.3

0.32

0.34

0.36

Test C1.12

Vin=80V

Ibus=0.5A-3.5A

Bus voltage is properly regulated under current steps (droop effect)

0.38

Control. Single module: MPPT



Universidad Carlos III de Madrid



Test C1.16

Vin=PV panel emulator (MP=240W)

Vbus=100V (regulated by the load)

MPPT produces expected input voltage variations



-0.6

-04

-0.2

Λ

0.2

0.6

0.8

1.2

Control. Three module set-up

- Every module has the same power stage and control stage
- Minimum control configuration made by external signals (switches)
- Simplified DC/DC modules



Universidad de Oviedo

Universidá d'Uviéu

University of Oviedo

Universidad

Carlos III de Madrid



Control. Three module: bus current sweep



e Oviedo Uviéu Oviedo Universidad Carlos III de Madrid



Test C3.4

Vin=80 V

Ibus=2-9A

Module priorization as expected using DC bus signalling

10

6

Control. Three module: full test (MPPT and battery)







Test C3.12

Vin3=PV panel emulator (MP=240W), Vin1=battery, Iload=2-9A

MPPT in module 1 is always operating as it has to provide the load power and the battery charge

While module 2 is not saturated, battery is being charged. When module 2 reaches its maximum output current, battery module regulates the bus

Control. Three module: load current steps

Universidad de Oviedo Universidad ٦Ū Universidá d'Uviéu Carlos III de Madrid University of Oviedo







Overall test

Control. Three module: supervisor set-up







For simplicity, only connected to module 1

Control. Three module: telemetry







Supervisor gets telemetry data every second approx.

Offset in the measured data







Supervisor sends a command to change V-I curve parameters in module 1

Constant current bus during test: depending on the V-I curve module 3 or module 1 regulate the bus

Bus voltage is properly regulated despite the change in V-I curve

- Feasibility of making a primary power distribution system based on equal power modules, with the same digital control and only sharing the information of the bus voltage
- DC bus signalling is used to prioritized the modules that provide the energy to the load while keeping the bus regulated: SAR modules priority vs. Battery modules to deliver power to the load
- Although the result is a non-tight regulation of the bus, the variation of the bus voltage is less than 5%.
- The priority order of the modules can be changed by the external supervisor
- MPPT algorithm is running in SAR modules. When the module is in MPPT mode, the variable injected current is compensated by the regulating module
- Battery module can be charged and is the module that ensures bus regulation despite the operation condition of the other modules
- Extensive test demonstrates the implemented control
- Co-simulation has been a useful tool for control debugging



Health Monitoring of digitally controlled flexible converters

Health monitoring



Universidad Carlos III de Madrid





Universidad de Oviedo Universidá d'Uviéu University of Oviedo



- Health monitoring methods
 - Improve reliability
 - Increase lifetime
 - Modules able to recalculate power demands





- Failure causes:
 - Magnetic elements: Almost nothing reported.
 - Capacitors:
 - One of the main causes
 - Indicators include increased ESR and reduction of capacitance
 - · When modules sharing output difficult to identify which is failing.
 - Space design: Self-healing capacitors.
 - Semiconductor switches:
 - Main cause of failure
 - The ultimate root cause is in most cases mechanical and package related.
 - Multiple indicators
 - Mainly related to MOSFETs and IGBTs



- Multiple indicators:
 - Threshold voltage
 - Difficult to measure in application.
 - Body diode forward voltage
 - Difficult to measure in application.
 - Gate charge
 - Specialized circuitry. Difficult to measure in application.
 - Parasitic capacitances
 - Specialized circuitry. Difficult to measure in application.
 - Breakdown voltage
 - Difficult to measure in application. Potentially destructive.
 - Leakage current
 - Difficult to measure in application.
 - On-state resistance:
 - Most used method.
 - Possible to measure in application.

- Detect MOSFET degradation
 - Resistance increase
 - Non-invasive
- Three alternatives
 - Kalman filter
 - Model comparison based on heatmap
 - Machine learning









- MOSFET resistance measurement good indicator
- Direct measurement not an option
 - Added complexity. Reliability decreases
- Prediction
 - Kalman filter
 - Noisy environments, GNSS



Universidad de Oviedo

Universidá d'Uviéu

University of Ovieda

Universidad

Carlos III de Madrid



- State prediction based on previous inputs
 - State variables x_k
 - State transition matrix $x_{k+1} = f(x_k, u_k, w_k)$
 - Describes state evolution over time
 - Measurement model $z_k = h(x_k, v_k)$
 - State covariance P
 - · Uncertainty in the estimated state

- Process noise covariance Q
 - · Uncertainty in the process model
- Measurement noise covariance R
 - Uncertainty in sensors
- Kalman gain K
 - Weights that assign how much trust is given to measurements
- Jacobian matrices F_k and H_k



| | Correction Compute Kalman gain: | |
|--|--|--|
| | | |
| | $K[n] = P^{J}[n] J^{I}_{H}[n] ig(J_{H}[n] P^{J}[n] J^{I}_{H}[n] + R_{0} ig)^{-1}$ | |
| | Update estimate with measurement x^m $x^a[n] = x^f[n] + K_x[n]ig(x^m[n] - x^f[n]ig)$ | |
| | Update error covariance: $P^a[n] = [I-K[n]J_H[n]]P^f[n]$ | |



- Case of study: average current controlled boost converter
 - Adapted to Buck too
- Estimation of parasitic resistance

 V_{in} V_{in} V

- Control inputs
 - V_{in}, V_{out}
 - Current reference I_{ref}
 - Additional current sample I_{rip}
 - Duty cycle d
- Output:
 - Estimated states r_l and current ripple $\Delta i = I_{RIP} I_{REF}$



 V_o

- State variables
 - Current sample difference Δi
 - Parasitic resistance r_l
- State space description

$$\begin{bmatrix} \dot{\Delta}i \end{bmatrix} = A \cdot \begin{bmatrix} \Delta i \\ r_l \end{bmatrix} + B \cdot \begin{bmatrix} V_{in} \\ V_o \\ I_{ref} \end{bmatrix} \qquad A = -\frac{r_l}{L} \qquad B = \begin{cases} \begin{bmatrix} \frac{1}{L} & 0 & \frac{-r_l}{L} \end{bmatrix} \text{ when } 0 < t < d \cdot T_s \\ \begin{bmatrix} \frac{1}{L} & \frac{-1}{L} & \frac{-r_l}{L} \end{bmatrix} \text{ when } d \cdot T_s < t < T_s \end{cases}$$

- State transition
 - One switching cycle is developed

$$\Delta i(T_s) = e^{-\frac{r_l}{L}T_s} \cdot \Delta i(0) + \int_0^{T_s} e^{-\frac{r_l}{L}(T_s - \tau)} \cdot B(\tau) \cdot \begin{bmatrix} V_{in} \\ V_o \\ I_{ref} \end{bmatrix} d\tau$$







Next switching cycle

$$\Delta i(T_s) = \left(1 - \frac{r_l}{L}T_s\right)\Delta i(0) + \left(\frac{V}{L}\right)T_s - I_{ref}\frac{r_l}{L}T_s$$

• Boost $V[n] = V_{in}[n] - (1 - d[n]) \cdot V_o[n]$ • Buck $V[n] = d[n] \cdot V_{in}[n] - V_o[n]$

State transition

$$F(X[n], U[n]) = \begin{bmatrix} \Delta i[n] \\ r_l[n] \end{bmatrix} = \begin{bmatrix} \Delta i[n-1] \cdot \left(1 - r_l[n-1] \cdot \frac{T_s}{L}\right) + \frac{T_s}{L} \cdot (V[n-1]) - I_{ref}[n-1] \cdot \frac{T_s}{L} \cdot r_l[n-1] \\ r_l[n-1] \end{bmatrix}$$







| Parameter | Value |
|--|-----------------|
| Input voltage V_{in} : | 15 V |
| Output voltage V _o : | 30 V |
| Inductor <i>L</i> : | 275 µH |
| Capacitor C: | 570 μF |
| Switching frequency f_{sw} : | 10 <i>kHz</i> |
| Switching FET: | FDP26N40 |
| Switching FET ON resistance <i>R</i> _{dson} : | $190 \ m\Omega$ |
| Reference current <i>I_{ref}</i> : | 1.5 <i>A</i> |
| ADC resolution: | 12 bits |
| ADC input range: | 0-3V |

- Custom boost converter
- Data acquisition
 - Texas Instruments TMS28F379
- Kalman filter execution on external PC





- EKF prediction implementations
- Simulink model
 - Wide range of toolboxes
 - DSP support



DSP communication & data

| Parameter | Value |
|---|--|
| Initial states X_0 | $\begin{bmatrix} 0\\110\cdot 10^{-3}\end{bmatrix}$ |
| State error covariance matrix <i>P</i> ₀ : | $\begin{bmatrix} 1 \cdot 10^{-3} & 0 \\ 0 & 1 \cdot 10^{-3} \end{bmatrix}$ |
| Measurement noise <i>R</i> ₀ : | $1 \cdot 10^{-2}$ |
| Process noise <i>Q</i> : | $\begin{bmatrix} 1 \cdot 10^{-3} & 0 \\ 0 & 1 \cdot 10^{-3} \end{bmatrix}$ |



- Degradation simulated using MOSFET driver voltage change
 - 10% increase
- Change in conduction resistance detected
- Minor changes in input voltage cause errors in prediction.





Kalman filter:

- + Detection of parasitic resistance increase
- Second current sample needed
- Temperature effects not considered

- Four-switch buck boost
 - Gain= $\frac{D_1}{1-D_2}$
- Same gain, different duty cycles
- Regions where degradation is evident
- Operating in suboptimal conditions during certain moments (e.g. out of eclipse)





Universidad de Oviedo Universidá d'Uviéu University of Oviedo

Converter losses calculated





- Find zones of interest
 - Different degradations for each MOSFET



M1 aged



- Find zones of interest
 - Different degradations for each MOSFET





- Comparison with prototype
 - Temperature effects not considered
 - Not accurate



- Generating whole heatmap is resource consuming
- Generated database with different aging elements
- Baseline to predict behaviour






- Generated "real measurements
 - Random noise -> 5% measurement error
 - Detection





- Heatmap conclusions:
- Results inconclusive
- External errors (measurement, temperature effects...) have not been considered
- No additional measurements needed
 - Input/output power



- Machine Learning Approach:
 - Forget about any prior model
 - Just use data to model a healthy converter.
 - Inputs: Vin, Vout, Temperature, Iload,...
 - Outputs: Duty cycle command, inductor current ripple,
 - Neural Network fits the input data to the output. Generate a model of the converter.
 - Degradation-> Difference between model and measurements.
 - Significant difference: More than 1 standard deviation from average.





- Utilization of the approach
 - The model is specific for each unit.
 - The data could be qualification data
- Results of the activity
 - Input data identified
 - Converter indicators identified
 - Training datasets generated
 - Simulation only
 - Several estimators trained





- Dataset generation
 - Module simulation in PSIM. Scripts to vary Vin, Iload and Temperature
 - Including control scheme
 - Includes temperature effect on MOSFETs
 - Includes switching and driving losses





- Dataset generation
 - Measurements
 - Sampled at the switching rate and filtered





- Dataset generation
 - r_{ds_on} varies with temperature
 - Approximation of conduction and switching losses
 - Simple thermal model for switches
 - Degradation modelled as an increase of the r_{ds_on}
 - Inductor change only for a loss of 1 turn.
- Goal of model: Provide data. The data may not reflect accurately the reality.









• Dataset generation

- Change in r_{ds_on}
 - Converter labelled as degraded or non-degraded.
 - Non-degraded converters: increase in $r_{ds_on} < 25\%$.
 - Degraded converters: $1.5 \cdot r_{ds_on_nominal} \ge r_{ds_on} \ge 1.9 \cdot r_{ds_on_nominal}$.
- Change in inductance
 - Converter labelled as degraded or non-degraded.
 - Nominal inductance: 84 μ *H*
 - Degraded converters: Inductance lower than 84 μ H. Minimal 67.2 μ H
- Training is only performed over non-degraded data.



- Data for training:
 - 80% Training and Validation 20% Test
 - Training and Validation: 80% Training 20% Validation
 - Select a data subset 80% Training and Validation 20% Test for each of the temperatures in the test
 - Merge all the subsets
 - All the temperatures are represented in the dataset.



• Data for training:

- $V_{in} = 42 V$ and $V_{in} = 100 V$. $\Delta V_{in} = 1 V$
- $I_{load} = 2 A$ and $I_{load} = 6 A$. $\Delta I_{load} = 0.25 A$.
- $T_{base} = 40 \ ^{o}C$ and $T_{base} = 70 \ ^{o}C$. $\Delta T_{base} = 1 \ ^{o}C$. For evaluation $\Delta T_{base} = 3 \ ^{o}C$
- *r*_{ds_on} increase between 0 and 0.25 for training.
- *r*_{ds_on} increase between 0 and 0.9 for evaluation.
- Inductance between 67.2 μ *H* and 84 μ *H*. Δ *L* = 0.1 μ *H*



- Converter outputs to estimate:
 - Duty cycle
 - Normalized ripple











- NN structure
 - Tip: Every few layers constrict the width
 - NN as universal function approximators.
 - A network with infinite length has a minimum width of the number inputs plus 1.
 - Depth and width are free parameters
 - We constrict the network each 6 layers (free parameter)
 - Trial and error 13 layers, 29 neurons per layer, shrink to 5 every 6 layers)
 - Activation function Rectified Linear
 - Single output
 - A NN for estimating D
 - A NN for estimating Δi_{l_norm}

Universidad

Carlos III de Madrid

input: [(None, None

output: [(None, None)]

input: (None, None)

(None, 4)

output:

input: (None, 4)

output: (None, 4)

input: (None, 4)

output: (None, 29)

input: (None, 29)

output: (None, 29)

input: (None, 29)

Universidad de Oviedo

normalization_input | InputLayer

input | Dense

Dense

Dens

Dens

Normalization

ormalization

Universidá d'Uviéu

University of Oviedo

Output

Input



• Results:

• Identifying $r_{ds on}$ degradation through D cycle estimation





• Results:

• Identifying *L* degradation through Δi_{l_norm} estimation



- Universidad de Oviedo Universidá d'Uviéu University of Oviedo University of Oviedo
- Conclusions at the time of submitting the final report:
 - Changes in r_{ds_on} imply very subtle changes in Duty cycle.
 - The approach works well with bigger changes
 - Bigger increase in r_{ds_on}
 - Changes in Δi_{l_norm} due to L changes
- Before the final presentation changes were made
 - Activation function tanh
 - Inclusion of normalization stages
 - Amplify the duty cycle changes through estimating $e^{(1+D)}$



Predicted label

• Results:

• Identifying r_{ds_on} degradation through $e^{(1+D)}$ cycle estimation



Much better result. However more False Positives



- Conclusions of Machine Learning approach
 - Interesting results (after last changes)
 - Key failure indicators found
 - Much work to be done
 - Real converter data
 - Data resolution
 - NN structure and training
 - System implementation



- Health Monitoring conclusions
 - 3 techniques researched
 - Kalman Filter most mature
 - Manage temperature changes
 - Almost ready for implementation

- Heatmaps and Machine learning promising but at a very low maturity
 - A lot of work needs to be done

Final Conclusions

- Topology
 - Single power stage
 - 4 switch Buck Boost: SAR, BDR, CDR
 - GaN Based
 - High effciency
- Decentralized control
 - Based on DC bus signaling
 - 3 roles achieved (MPPT, battery charge,...)
 - Good bus regulation
 - Seamlesly transitions
- Health monitoring
 - 3 techniques researched
 - Premature yet interesting results



Health Monitoring of digitally controlled flexible converters

Thanks for the attention Questions?



Universidad Carlos III de Madrid





Universidad de Oviedo Universidá d'Uviéu University of Oviedo